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INFORMATION
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Atty. Docket No.: 150.0064 0102

Serial No.: 09/942,200

Applicant(s): Eugene P. Marsh

Confirmation No.: 8194

Filing Date: 29 August 2001

**Group: 2811** 

## U.S. PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
JN		3,839,164	10/01/74	Hurst			
		4,830,982	05/16/89	Dentai et al.			
		4,992,305	02/12/91	Erbil			
		5,045,899	09/03/91	Arimoto			
		5,096,737	03/17/92	Baum et al.			
		5,130,172	07/14/92	Hicks et al.			
		5,149,596 •	09/22/92	Smith et al.			
		5,187,638	02/16/93	Sandhu et al.			
		5,198,386	03/30/93	Gonzalez			
		5,232,873	08/03/93	Geva et al.			
		5,252,518	10/12/93	Sandhu et al.			
		5,270,241	12/14/93	Dennison et al.			
		5,341,016	08/23/94	Prall et al.			
		5,354,712	10/11/97	Ho et al.			
	]	5,362,632	11/08/94	Mathews			
		5,372,849	12/13/94	McCormick et al.			
		5,392,189	02/21/95	Fazan et al.			
		5,403,620	04/04/95	Kaesz et al.			
		5,464,786	11/07/95	Figura et al.			
		5,466,629	11/14/95	Mihara et al.			
		5,478,772	12/26/95	Fazan			
		5,480,684	01/02/96	Sandhu			
		5,487,923	01/30/96	Min et al.			
		5,498,562	03/12/96	Dennison et al.			

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JOSEPH NEUYEN	6/6/02

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INFORMATION
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Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
JN		5,506,166	04/09/96	Sandhu et al.			
		5,510,651	04/23/96	Maniar et al.			
		5,520,992	05/28/96	Douglas et al.			
		5,555,486	09/10/96	Kingon et al.			
		5,561,307	10/01/96	Mihara et al.			
		5,566,045	10/15/96	Summerfelt et al.			
	Х	5,587,436•	12/03/96	Summerfelt et al.			
		5,599,424	02/04/97	Matsumoto et al.			
		5,605,857	02/25/97	Jost et al.			
		5,618,746	04/08/97	Hwang			
		5,637,527	06/10/97	Baek			
		5,639,698	06/17/97	Yamazaki et al.			
		5,652,171	07/29/97	Nagano et al.	:		
		5,654,222	08/05/97	Sandhu et al.			
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		5,661,115	08/26/97	Sandhu			
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		5,679,225	10/21/97	Pastacaldi et al.			
		5,679,980	10/21/97	Summerfelt			
		5,691,009	11/25/97	Sandhu			
	X	5,691,219	11/25/97	Kawakubo et al.			
		5,695,815	12/09/97	Vaartstra			
		5,696,384	12/09/97	Ogi et al.			
		5,714,402	02/03/98	Choi			
		5,717,250	02/10/98	Schuele et al.			

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JN		5,728,626	03/17/98	Allman et al.			
		5,744,832	04/28/98	Wolters et al.			
		5,760,474	06/02/98	Schuele			
		5,962,716	10/05/99	Uhlenbrock et al.			
		5,970,378	10/19/99	Shue et al.			
		5,972,105	10/26/99	Yamazaki et al.			
		5,990,559	11/23/99	Marsh			
		6,063,705	05/16/00	Vaartstra			
		6,074,945	06/13/00	Vaartstra et al.			
		6,127,257	10/03/00	Pintchovski et al.			
		6,133,159	10/17/00	Vaartstra et al.			
	X	6,140,173	10/31/00	Wolters et al.			
		6,204,172 B1	03/20/01	Marsh			
	X	6,323,081 B1 •	11/27/01	Marsh			

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Examiner	Сору	Document Number	Date	Country	Class	Subclass	Trans	lation
Initial	Enclosed						Yes	No
JN		DE 197 37 323 A1	03/11/99	Germany				
		0 301 725 A2	02/01/89	EPO				
		0 770 862	05/02/97	EPO				
		9 162372	06/20/97	Japan				
	X	WO 00/14778 •	03/16/00	PCT				

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

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JN		Al-Shareef et al., "Analysis of the oxidation kinetics and barrier layer properties of ZrN and Pt/Ru thin films for DRAM applications", <i>Thin Solid Films</i> , 280, 265-270 (1996).
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		Hsu et al., "Synthesis and X-ray structure of the heteronuclear cluster, $(\mu-H)_2(\eta^5-C_5H_5)$ IrOs <sub>3</sub> (CO) <sub>10</sub> ," Journal of Organometallic Chemistry, 426, 121-130 (1992).
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24		Kaesz et al., "Low-Temperature Organometallic Chemical Vapor Deposition of Transition Metals," <i>Mat. Res. Soc. Symp. Proc.</i> , 131, 395-400 (1989).
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		Niemer, B., et al., "Organometallic chemical vapor deposition of tungsten metal, and suppression of carbon incorporation by codeposition of platinum," <i>Appl. Phys. Lett.</i> , 61(15):1793-1795 (1992).
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<b>1</b> 1 1 1		Smith et al., "Low-Temperature Chemical Vapor Deposition of Rhodium and Iridium Thin Films," <i>Mat. Res. Soc. Symp. Proc.</i> , 168, 369-374 (1990).			
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